# CRMEP18N20B

#### N-Channel 200V, 134mΩ Typ. Power MOSFET

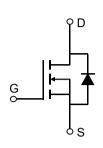
## **Description**

#### **Features**

• 200V, 18A

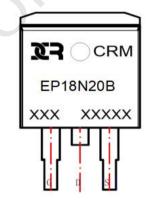
 $R_{DS(ON)}$  Typ = 134m $\Omega$  @  $V_{GS}$  = 10V

- Fast Switching
- Improved dv/dt Capability
- 100% UIS TESTED!
- 100% ΔVds TESTED!





# D



Initial Version: 1.0

**Marking and Pin Assignment** 

# **Application**

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)

**Package Marking and Ordering Information** 

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMEP18N20B	CRMEP18N20B	TO-263-3L	TAPING	13"	800	4800

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#### Absolute Maximum Ratings (@ T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
$V_{DS}$	Drain-to-Source Voltage		200	V
$V_{GS}$	Gate-to-Source Voltage		±20	V
	Continuous Drain Current	T <sub>C</sub> = 25°C	18	А
I <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> = 100°C	10.8	А
I <sub>DM</sub>	Pulsed Drain Current (1)		72	А
E <sub>AS</sub>	Single Pulsed Avalanche Energy (2)		169	mJ
$P_{D}$	Power Dissipation	T <sub>C</sub> = 25°C	150	W
$R_{ heta JC}$	Thermal Resistance, Junction to Case		0.83	°C/W
$T_{J}$ , $T_{STG}$	Junction & Storage Temperature Range		-55 to 150	°C

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#### **Electrical Characteristics** (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Chara	acteristics					
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	200	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V	-	-	1.0	μА
I <sub>GSS</sub>	Gate-Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±100	nA
On Chara	acteristics				6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	V
R <sub>DS(ON)</sub>	Static Drain-Source ON-Resistance <sup>(3)</sup>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A	-	134	174	mΩ
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance		- /	911	-	pF
$C_{oss}$	Output Capacitance	$V_{GS} = 0V, V_{DS} = 25V,$ f = 1MHz	-	165	-	pF
$C_{rss}$	Reverse Transfer Capacitance	1 – 11VII 12	X-\	87	-	pF
$Q_g$	Total Gate Charge		-	60	-	nC
$Q_gs$	Gate Source Charge	$V_{GS} = 0 \text{ to } 10V$ $V_{DS} = 160V, I_{D} = 18A$	<b>)</b>	4	-	nC
$Q_{gd}$	Gate Drain("Miller") Charge	V <sub>DS</sub> = 100 V, I <sub>D</sub> = 10A	-	37	-	nC
Switchin	g Characteristics					
$t_{d(on)}$	Turn-On DelayTime		-	12	-	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10V, V_{DD} = 100V$	-	145	-	ns
$t_{d(off)}$	Turn-Off DelayTime	$I_D$ = 18A, $R_{GEN}$ = $5\Omega$	-	50	-	ns
$\mathbf{t}_{f}$	Turn-Off Fall Time		-	15	-	ns
Orain-So	urce Diode Characteristics and N	Max Ratings				
I <sub>s</sub>	Maximum Continuous Drain to Source Diode Forward Current			-	18	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode	Forward Current	-	-	72	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 9A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	1 - 400 4:/4+ - 4000/-	-	200	-	ns
Qrr	Body Diode Reverse Recovery Charge	I <sub>F</sub> = 18A, di/dt = 100A/us	-	1.2	-	nC

Notes:

<sup>1.</sup> Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

<sup>2.</sup>  $E_{AS}$  condition: Starting  $T_J$ =25°C,  $V_{DD}$ =50V,  $V_G$ =10V,  $R_G$ =25ohm, L=0.5mH,  $I_{AS}$ =26A

<sup>3.</sup> Pulse Test: Pulse Width  $\!\!\leqslant\! 300\mu s,$  Duty Cycle  $\!\!\leqslant\! 0.5\%.$ 

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#### **Test Circuit**

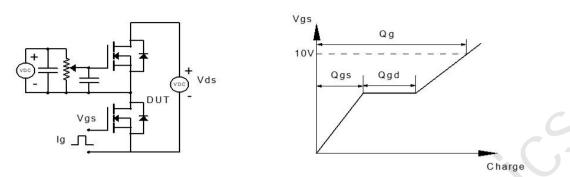


Figure 1: Gate Charge Test Circuit & Waveform

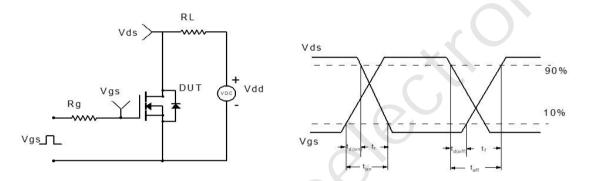


Figure 2: Resistive Switching Test Circuit & Waveform

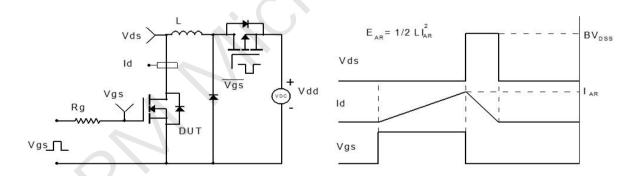


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

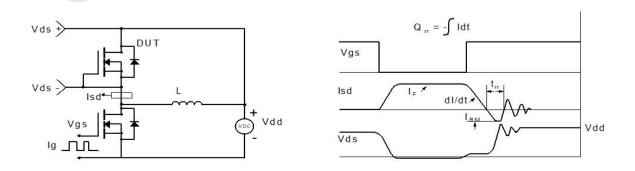
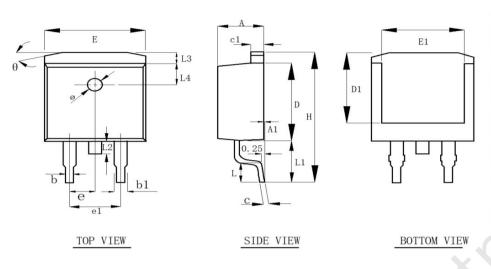


Figure 4: Diode Recovery Test Circuit & Waveform

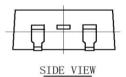
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### Package Mechanical Data(TO-263-3L)



	COMMON DIMENSIONS (UNITS OF MEASURE=mm)				
SYMBOL	MIN	NOM	MAX		
A	4.30	4. 50	4.70		
A1	0.00	NA	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.30	1.40		
С	0.40	0.47	0.55		
c1	1. 25	1. 30	1.35		
D	9. 00	9. 10	9. 20		
D1	8.00	8. 10	8. 20		
Н	14. 90	15. 20	15. 50		
Е	9. 80	10.00	10. 20		
E1	7. 85	8. 00	8. 15		
e1	4. 93	5. 08	5. 23		
L	2.00	2. 20	2.45		
L1	4. 60	4.80	5. 00		
L2	1.30	1.50	1.70		
L3	1.15	1. 25	1.35		
L4	2.40	2.50	2.60		
Ø	1.5 REF				
е	2.54 BSC				
θ	13° TYP				



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